





LOW $V_{\text{CE(SAT)}}$ PNP SURFACE MOUNT TRANSISTOR

Features

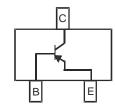
- **Epitaxial Planar Die Construction**
- Ideal for Medium Power Amplification and Switching
- Complimentary NPN Type Available (DNLS320A)
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



SOT-23



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-20	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I _{CM}	-5	A
Repetitive Peak Pulse Current (Note 3)	I _{CRP}	-3	Α
Continuous Collector Current	I _C	-2	A
Base Current	I _B	-0.5	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ T _A = 25°C	P _D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 3) @ T _A = 25°C	$R_{ hetaJA}$	209	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Operated under pulsed conditions: pulse width ≤100ms, duty cycle ≤ 0.25.
- 4. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions	
OFF CHARACTERISTICS (Note 5)							
Collector-Base Cutoff Current	1		_	-100	nA	$V_{CB} = -20V, I_{E} = 0$	
Collector-base Cuton Current	Ісво	_	_	-50	μА	V _{CB} = -20V, I _E = 0, T _A = 150°C	
Emitter-Base Cutoff Current	I _{EBO}	_	_	-100	nA	$V_{EB} = -5V, I_{C} = 0$	
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-20	_	_	V	$I_C = -100 \mu A$	
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-20	_	_	V	I _C = -10mA	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	_	_	V	$I_E = -100 \mu A$	
ON CHARACTERISTICS (Note 5)							
		220	_	_		$V_{CE} = -2V, I_{C} = -0.1A$	
		220	_	_		$V_{CE} = -2V, I_{C} = -0.5A$	
DC Current Gain	h _{FE}	200	_	_	_	$V_{CE} = -2V, I_{C} = -1A$	
		150	_	_		$V_{CE} = -2V, I_{C} = -2A$	
		100	_	_		$V_{CE} = -2V, I_{C} = -3A$	
	V _{CE(SAT)}			-80		$I_C = -0.5A$, $I_B = -50mA$	
		_	_	-150		$I_C = -1A$, $I_B = -50mA$	
Collector-Emitter Saturation Voltage			_	-250	mV	$I_C = -2A$, $I_B = -100mA$	
		1	_	-230		$I_C = -2A$, $I_B = -200mA$	
			_	-330		$I_C = -3A$, $I_B = -300mA$	
Equivalent On-Resistance	R _{CE(SAT)}		90	115	mΩ	$I_E = -2A$, $I_B = -200mA$	
Base-Emitter Saturation Voltage		_	_	-1.1	V	$I_C = -2A$, $I_B = -100mA$	
base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	-1.2	V	$I_C = -3A$, $I_B = -300mA$	
Base-Emitter Turn-on Voltage	V _{BE(ON)}	_	_	-1.2	V	V _{CE} = -2V, I _C = -1A	
SMALL SIGNAL CHARACTERISTICS							
Transition Frequency	f _T	100	215	_	MHz	$V_{CE} = -5V, I_{C} = -100mA,$ f = 100MHz	
Output Capacitance	C _{ob}	_	_	50	pF	V _{CB} = -10V, f = 1MHz	

Notes: 5. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.

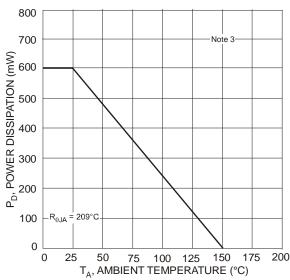


Fig. 1, Max Power Dissipation vs. Ambient Temperature

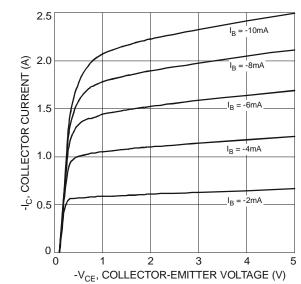


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage



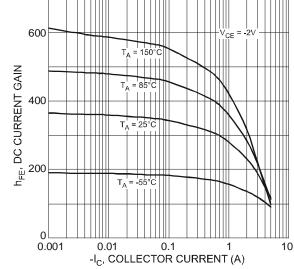


Fig. 3 Typical DC Current Gain vs. Collector Current

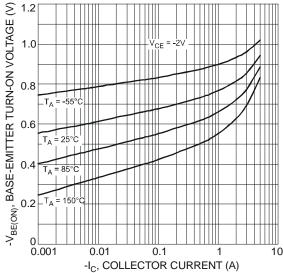
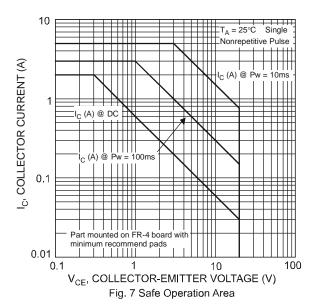
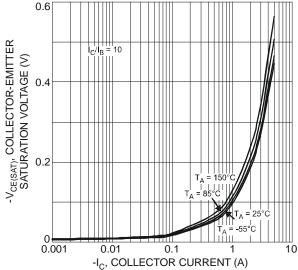


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current





-I_C, COLLECTOR CURRENT (A)
Fig. 4 Typical Collector-Emitter Saturation Voltage
vs. Collector Current

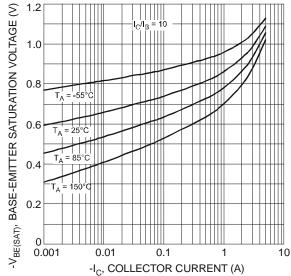


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

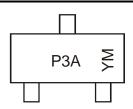


Ordering Information (Note 6)

Device	Packaging	Shipping
DPLS320A-7	SOT-23	3000/Tape & Reel

6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

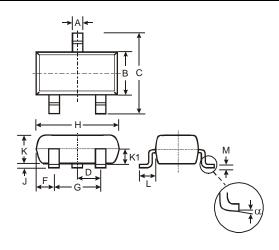


P3A = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008)M = Month (ex: 9 = September)

Date Code Key

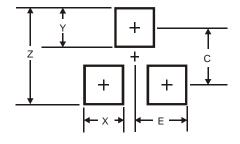
Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SOT-23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K 1	-	-	0.400			
L	0.45	0.61	0.55			
М	0.085	0.18	0.11			
α	0°	8°	-			
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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>>Diodes Incorporated(达迩科技(美台))